

Abstract

LOWER ELECTRODE OF DRAM CAPACITOR AND MANUFACTURING METHOD THEREOF

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A lower electrode is made of a TiN-based material and provided at a base of a dielectric film in a DRAM capacitor. The lower electrode includes first TiON films provided at opposite outer sides, the first TiON films having a relatively low oxygen concentration, and a second TiON film provided between the first TiON films, the second TiON film having a relatively high oxygen concentration.

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FIG. 1G

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